

N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I_D (A) ^a	Q_g (Typ.)
60	3.8 at $V_{GS} = 10$ V	80	98 nC

FEATURES

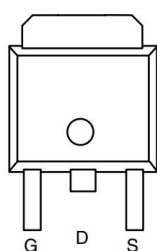
- 175 °C Junction Temperature
- DT-Trench Power MOSFET

APPLICATIONS

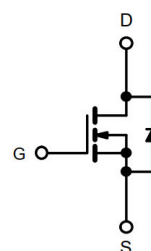
- Notebook PC Core
- VRM/POL



TO-252



Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 175$ °C)	$T_C = 25$ °C	I_D	80 ^{b, c}	A
	$T_C = 70$ °C		70 ^{b, c}	
Pulsed Drain Current		I_{DM}	240	
Avalanche Current Pulse	L = 0.1 mH	I_{AS}	85	
Single Pulse Avalanche Energy		E_{AS}	250	mJ
Continuous Source-Drain Diode Current	$T_C = 25$ °C	I_S	80 ^a	A
Maximum Power Dissipation	$T_C = 25$ °C	P_D	180 ^{b, c}	W
	$T_C = 70$ °C		115 ^{b, c}	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	$t \leq 10$ s	R_{thJA}	11	15	°C/W
Maximum Junction-to-Case	Steady State	R_{thJC}	0.75	1.0	

Notes:

a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

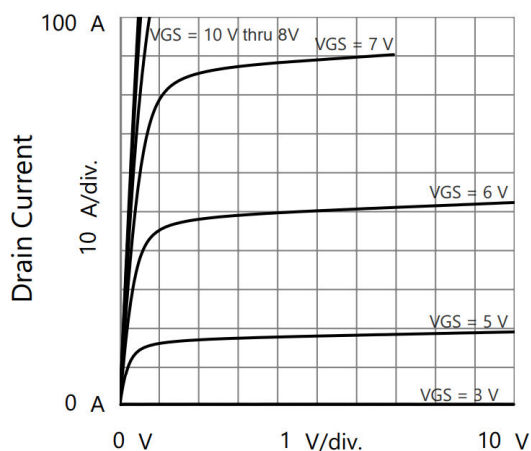
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min .	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	60			V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1		3.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60 V, V _{GS} = 0 V			1	μA
		V _{DS} =60 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	100			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		3.8	4.5	mΩ
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 10 A		80		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 30 V, V _{GS} = 0 V, f = 1 MHz		6200		pF
Output Capacitance	C _{oss}			430		
Reverse Transfer Capacitance	C _{rss}			430		
Total Gate Charge	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 10 A		98		nC
Gate-Source Charge	Q _{gs}			17		
Gate-Drain Charge	Q _{gd}			28		
Gate Resistance	R _g	f = 1 MHz		1.3		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, R _L = 0.6 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 2.5 Ω		18		ns
Rise Time	t _r			20		
Turn-Off Delay Time	t _{d(off)}			25		
Fall Time	t _f			10		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			80	A
Pulse Diode Forward Current ^a	I _{SM}				240	
Body Diode Voltage	V _{SD}	I _S = 1 A		0.6	1	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C		30		ns
Body Diode Reverse Recovery Charge	Q _{rr}			80		nC

Notes:

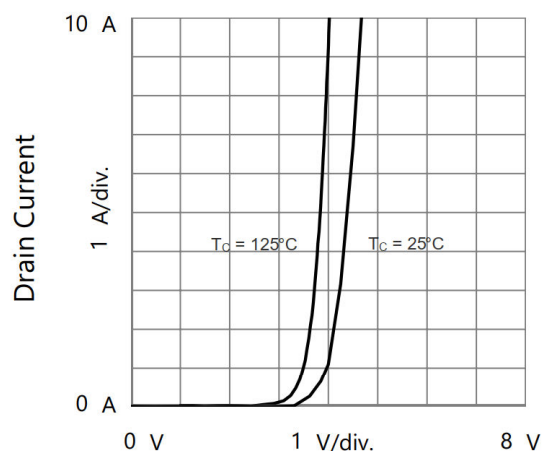
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

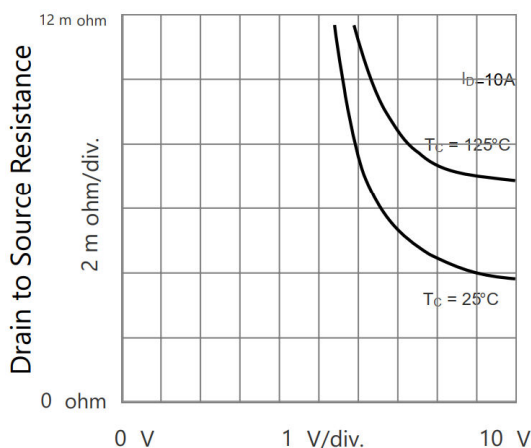
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



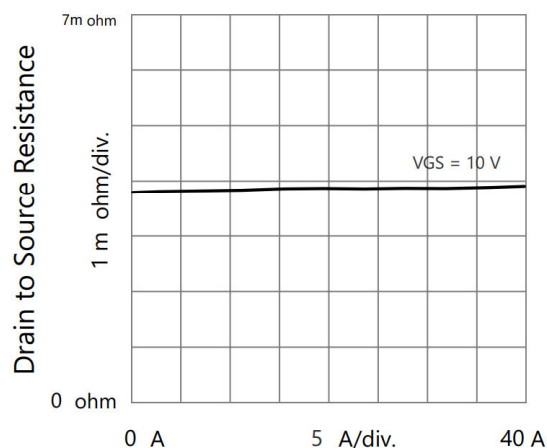
Drain to Source Voltage
Output Characteristics



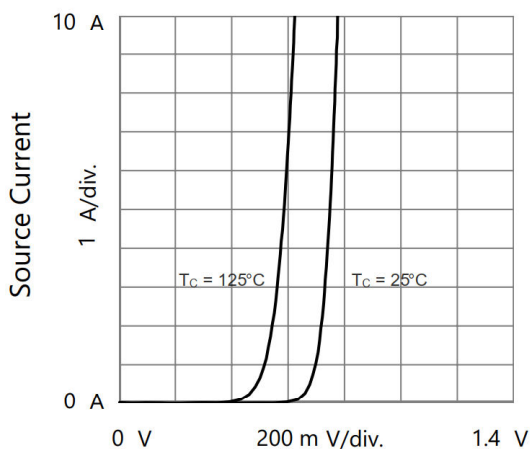
Gate to Source Voltage
Transfer Characteristics



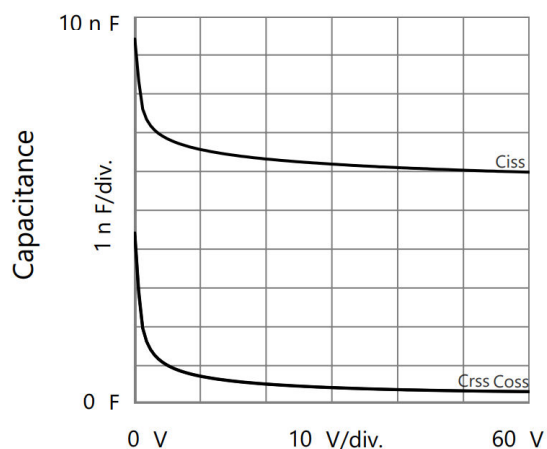
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

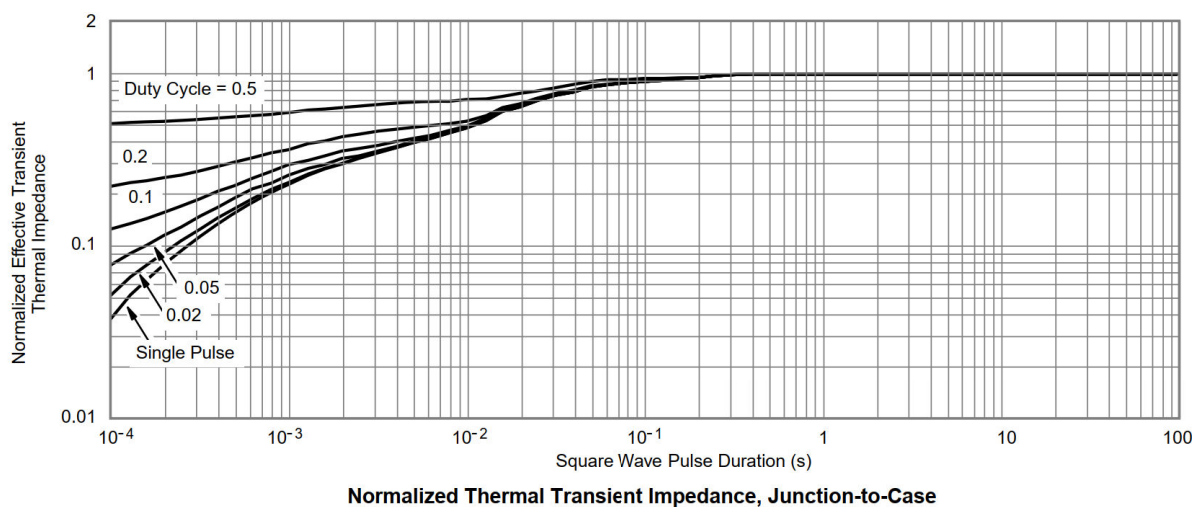
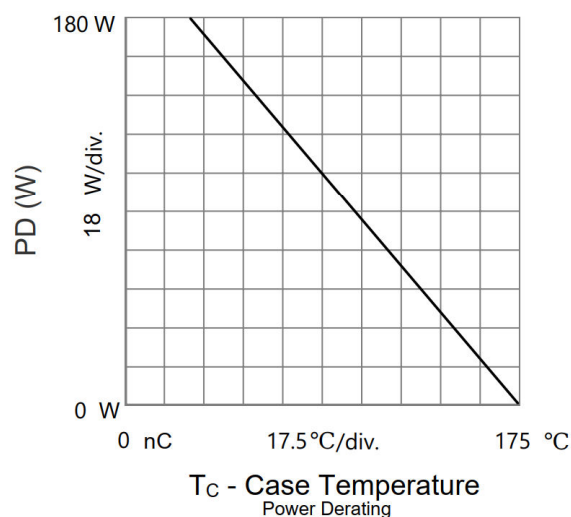
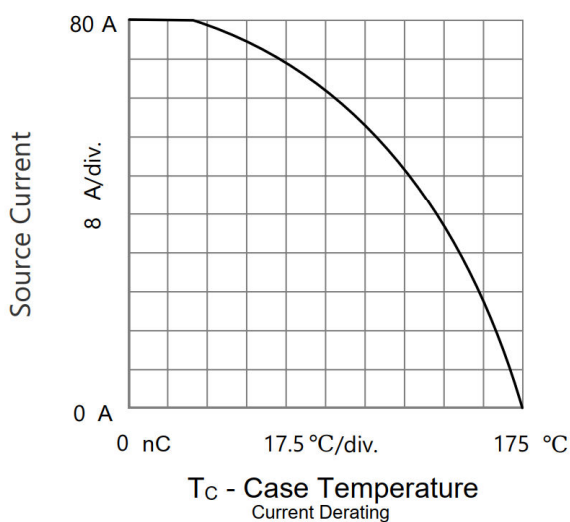
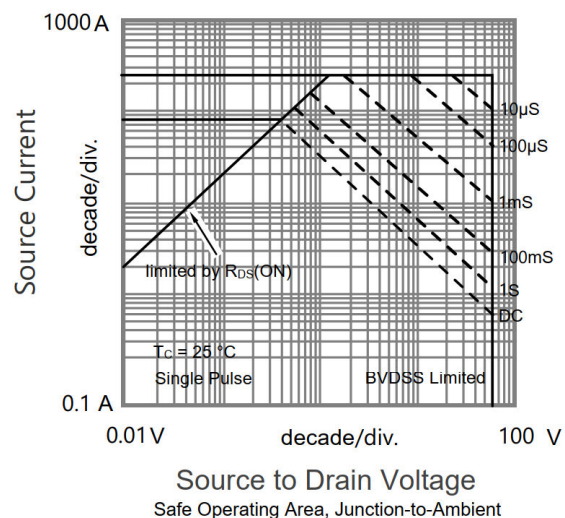
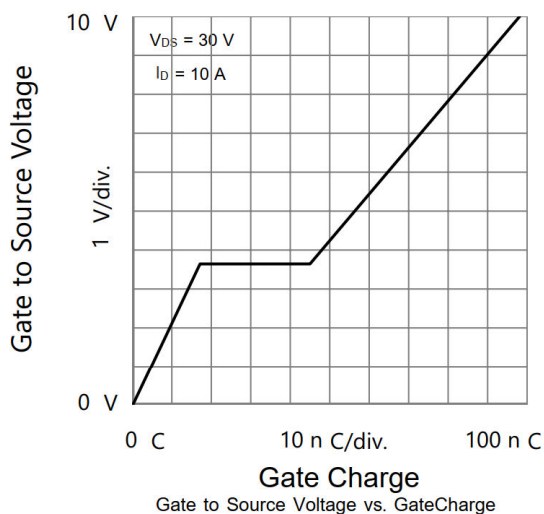


Source to Drain Voltage
Body Diode Forward Characteristics



Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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